

NPN Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 3.0 A continuous. Sourced from Process NB.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--------------------------------------------------|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 30 | V |
| V _{CBO} | Collector-Base Voltage | 50 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 3.0 | A |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | Units |
|-----------------|-----------------------------------------|------------------|-------|
| | | FPN330 / FPN330A | |
| PD | Total Device Dissipation | 1.0 | W |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 50 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 125 | °C/W |

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NPN Low Saturation Transistor (continued)

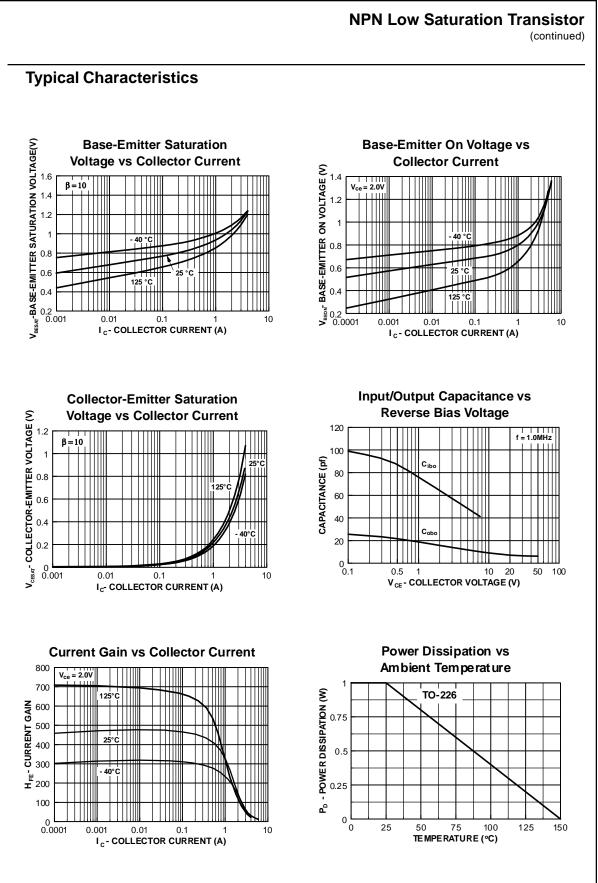
| Symbol | Parameter | Test Conditions | Min | Мах | Units |
|-------------------|----------------------------------------|-------------------------------------------------------------------------------------------------|-----|-----------|----------|
| OFF CHA | RACTERISTICS | | | | |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$ | 30 | | V |
| ВV _{CBO} | Collector-Base Breakdown Voltage | $I_{\rm C} = 100 \ \mu A, \ I_{\rm E} = 0$ | 50 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = 100 \ \mu A, I_C = 0$ | 5.0 | | V |
| I _{CBO} | Collector Cutoff Current | $V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ | | 100 10 | nA μA |
| I _{EBO} | Emitter Cutoff Current | $V_{EB} = 4.0 \text{ V}, I_{C} = 0$ | | 100 | nA |

| h _{FE} | DC Current Gain | $I_{C} = 100 \text{ mA}, V_{CE} = 2.0 \text{ V}$ | 330 | 100 | | |
|----------------------|--------------------------------------|---------------------------------------------------------|------|-----|------|----|
| | | | 330A | 250 | | |
| | | $I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | 120 | | |
| | | $I_{C} = 2.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | 50 | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{\rm C} = 1.0 \text{ A}, I_{\rm B} = 100 \text{ mA}$ | 330 | | 500 | mV |
| | | | 330A | | 450 | mV |
| | | $I_{\rm C} = 2.0 \text{ A}, I_{\rm B} = 200 \text{ mA}$ | | | 1.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 1.0 A, I _B = 100 mA | | | 1.25 | V |
| V _{BE(on)} | Base-Emitter Saturation Voltage | $I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | | 1.0 | V |

SMALL SIGNAL CHARACTERISTICS

| Cobo | Output Capacitance | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ | | 30 | pF |
|------|----------------------|------------------------------------------------------------------|-----|----|-----|
| FT | Transition Frequency | I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz | 100 | | MHz |

*Pulse Test: Pulse Width \leq 300 $\mu s, \, Duty \, Cycle \leq 2.0\%$



FPN330 / FPN330A

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|--------------------------|---------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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